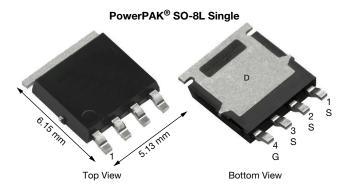
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Automotive P-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	-30
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.0092
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.0146
I _D (A)	-30
Configuration	Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

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(for detailed order number please see www.vishay.com/doc?79771)



RoHS COMPLIANT HALOGEN FREE

Configuration	Single	D P-Channel MOSFET			
ORDERING INFORM	ATION				
Package		PowerPAK SO-8L			
Lead (Pb)-free and halogen-f	ree	SQJA37EP			

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-30	V	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current ^a	T _C = 25 °C	I_	-30		
	T _C = 125 °C	I _D	-30		
Continuous source current (diode conduction) ^a		I _S	-30	А	
Pulsed drain current ^b		I _{DM}	-120		
Single pulse avalanche current			-26		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	33.8	mJ	
Maximum power dissipation ^b	T _C = 25 °C	P	45	w	
	T _C = 125 °C	P _D	15		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175		
Soldering recommendations (peak temperature) ^{d, e}			260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	70	°C/W
Junction-to-case (drain)		R _{thJC}	3.3	0/₩

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static		•						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = -250 \ \mu A$		-30	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V_{GS} , I_D = -250 μ A	-1.5	-2.0	-2.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 175 °C	-	-	-200		
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge -5 V$	-20	-	-	А	
		V _{GS} = -10 V	I _D = -6 A	-	0.0076	0.0092		
_	_	V _{GS} = -10 V	I _D = -6 A, T _J = 125 °C	-	-	0.0112		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -6 A, T _J = 175 °C	-	-	0.0122	Ω	
		V _{GS} = -4.5 V	I _D = -5 A	-	0.0120	0.0146	1	
Forward transconductance b	9 _{fs}	V _{DS}	= -15 V, I _D = -6 A	-	32	-	S	
Dynamic ^b						<u> </u>	1	
Input capacitance	Ciss			-	3620	4900		
Output capacitance	Coss	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	360	500	рF	
Reverse transfer capacitance	C _{rss}			-	346	470		
Total gate charge ^c	Qq			-	65	100		
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	V _{DS} = -15 V, I _D = -5 A	-	9	-	nC	
Gate-drain charge ^c	Q _{qd}	_		-	12	-		
Gate resistance	R _q	f = 1 MHz		2.4	4.8	7.2	Ω	
Turn-on delay time ^c	t _{d(on)}			-	12	20		
Rise time ^c	t _r	- Voo	= -15 V, R _I = 3 Ω	-	4	10		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -5 \text{ A}, V_{GEN} = -10 \text{ V}, \text{ R}_g = 1 \Omega$		-	64	100	- ns	
Fall time ^c	t _f			-	24	40		
Source-Drain Diode Ratings and Charac	teristics b						L	
Pulsed current ^a	I _{SM}			-	-	-120	А	
Forward voltage	V _{SD}	I _F =	-6 A, V _{GS} = 0 V	-	-0.78	-1.2	V	
Body diode reverse recovery time	t _{rr}			-	22	45	ns	
Body diode reverse recovery charge	Q _{rr}		A, di/dt = 100 A/µs	-	11	25	nC	
Reverse recovery fall time	ta	I _F = -4	A, u/ul = 100 A/µs	-	11	-	ns	
Reverse recovery rise time	t _b			-	11	-	115	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.9	-	А	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

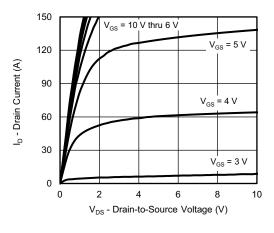
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

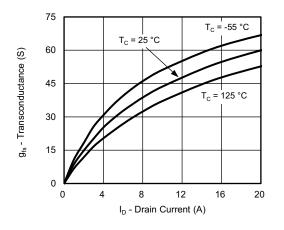
2



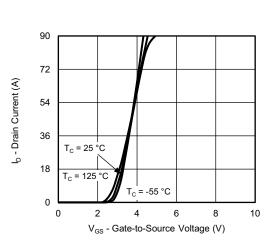
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



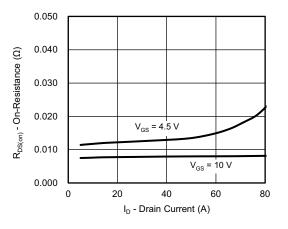
Output Characteristics



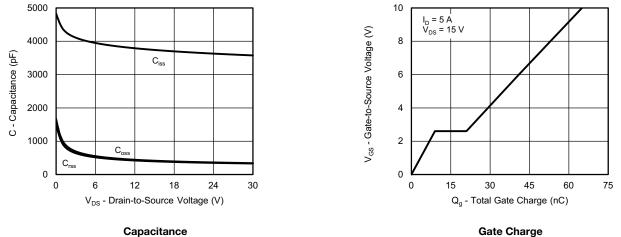
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



Capacitance

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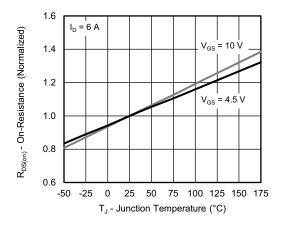
3

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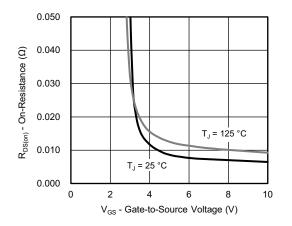
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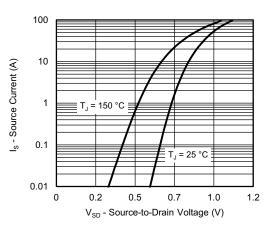
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



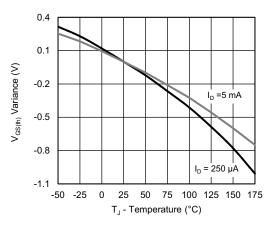
On-Resistance vs. Junction Temperature



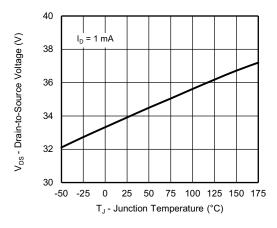
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage



Drain-Source Breakdown vs. Junction Temperature

4

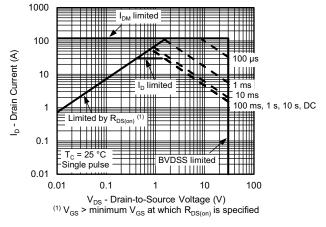
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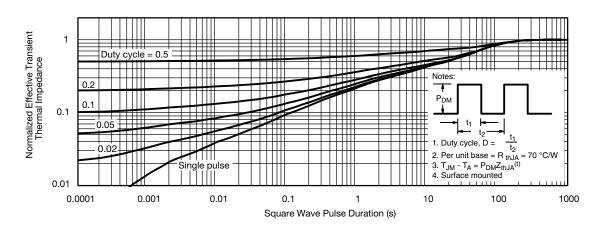
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THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

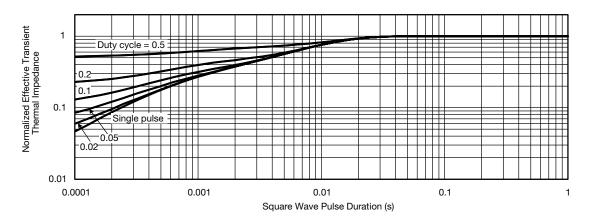


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THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

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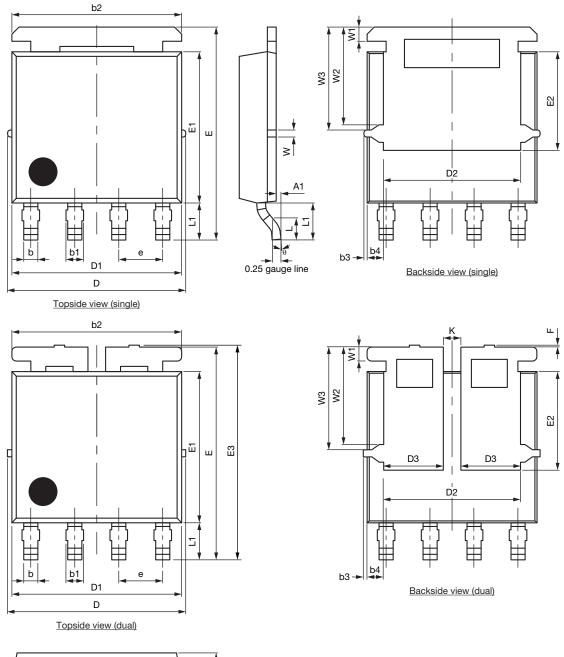
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

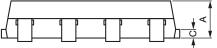
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75171.









Package Information



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DIM.		MILLIMETERS			INCHES			
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
E3	6.05	6.22	6.40	0.238	0.245	0.252		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51			0.020			
W		0.23		0.009				
W1		0.41		0.016				
W2		2.82		0.111				
W3		2.96		0.117				
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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